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Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	0	flexible near circuit adj board and wire and pads and shield near grounding	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR .	ON	2005/02/14 15:15
L2	80	flexible near circuit adj board and wire and pads and shield	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/14 15:15
S57	2	"5969422".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/14 08:48
S58	0	semiconductor adj device and recess and insulation and copper and Ru and wire and (438/687; 438/685; 438/681 ; 438/678; 438/675; 438/674; 438/668; 438/666; 438/654; 438/618; 438/656; 257/754; 257/762 ; 257/764; 257/766; 257/768; 257/770; 257/753; 257/741; 257/748 ; 257/769).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/14 08:54
S59	147	semiconductor adj device and recess and insulation and (438/687; 438/685; 438/681; 438/678; 438/675; 438/674; 438/668; 438/666; 438/654; 438/618; 438/656; 257/754; 257/762; 257/764; 257/766; 257/768; 257/770; 257/753; 257/741; 257/748; 257/769).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/14 08:54
S60	1	semiconductor adj device and recess and insulation and (438/687; 438/685; 438/681; 438/678; 438/675; 438/674; 438/668; 438/666; 438/654; 438/618; 438/656; 257/754; 257/762; 257/764; 257/766; 257/768; 257/770; 257/753; 257/741; 257/748; 257/769).ccls. and "29"/\$. ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/14 08:58
S61	72	semiconductor adj device and recess and insulation and "29"/\$.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/14 08:59
S62	0	semiconductor adj device and recess and insulation and "29"/\$.ccls. and recess near insulation near film	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/14 09:01

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S63	72	semiconductor adj device and recess and insulation and "29"/\$.ccls. and recess	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/14 09:06
S64	3	semiconductor adj device and recess and insulation and metal adj oxide and "29"/\$.ccls. and recess	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/14 09:07
S65	5	("4758927"   "4888307"   "5949649"   "6091341"   "6362964").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/02/14 09:07
S66	0	semiconductor adj device and recess and insulation and metal adj oxide and recess near "in insulation"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/14 09:08
S67	464	semiconductor adj device and recess and insulation and metal adj oxide and recess	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/14 09:08
S68	61	semiconductor adj device and recess and insulation and metal adj oxide and recess and conductive adj film	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/14 09:12
S69	1	semiconductor adj device and recess and insulation and metal adj oxide and recess and conductive adj film and (427/38; 427/39; 156/643; 156/646; 156/653; 156/657; 156/662; 156/345; 204/164; 204/192EC; 204/192E; 204/298; 252/79.1).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/14 11:23
S70	82	Mitsuru near Sekiguchi.inv.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/14 11:24
S71	0	Mitsuru near Sekiguchi.inv. and S59	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/14 15:14